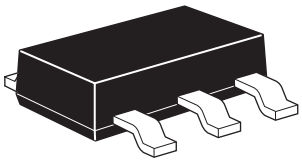
ZXMP6A16K
60V DPAK P-channel enhancement mode MOSFET

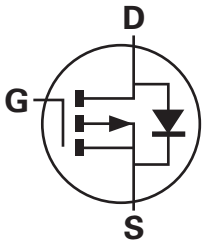
Summary



$V_{(BR)DSS}$	$R_{DS(on)}$ (Ω)	I_D (A)
-60	0.085 @ V_{GS}= -10V	8.2
	0.125 @ V_{GS}= -4.5V	6.75

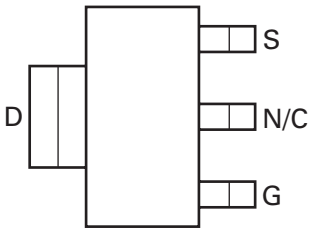
Description

This new generation trench MOSFET from Zetex features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.



Features

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- DPAK package



Pinout - top view

Applications

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP6A16KTC	13	16	2500

Device marking

ZXMP
6A16

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain-source voltage	V_{DSS}	-60	V
Gate-source voltage	V_{GS}	± 20	V
Continuous drain current @ V_{GS}= 10V; T_{amb}=25°C(b)	I_D	8.2	A
@ V_{GS}= 10V; T_{amb}=70°C(b)		6.5	
@ V_{GS}= 10V; T_{amb}=25°C(a)		5.4	
Pulsed drain current(c)	I_{DM}	27.2	A
Continuous source current (body diode)(b)	I_S	10	A
Pulsed source current (body diode)(c)	I_{SM}	27.2	A
Power dissipation at T_{amb} =25°C(a)	P_D	4.24	W
Linear derating factor		33.9	mW/°C
Power dissipation at T_{amb} =25°C(b)	P_D	9.76	W
Linear derating factor		78	mW/°C
Power dissipation at T_{amb} =25°C(d)	P_D	2.11	W
Linear derating factor		16.8	mW/°C
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient(a)	$R_{\Theta JA}$	29.45	°C/W
Junction to ambient(b)	$R_{\Theta JA}$	12.8	°C/W
Junction to ambient(d)	$R_{\Theta JA}$	59.1	°C/W

NOTES:

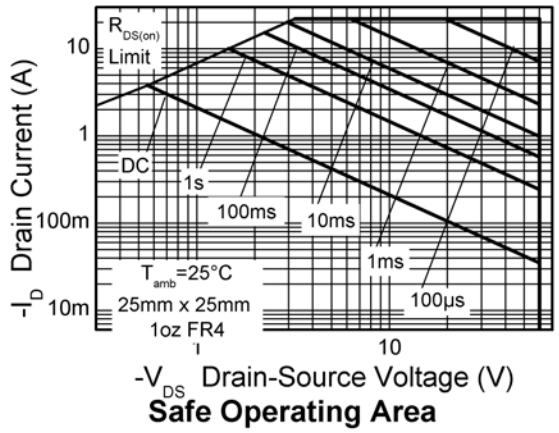
(a) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.

(b) For a device surface mounted on FR4 PCB measured at t ≤10 sec.

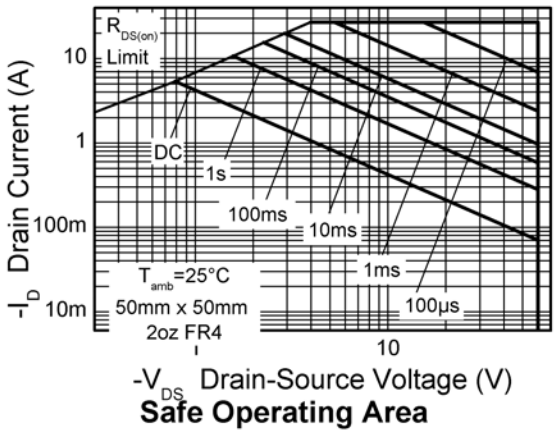
(c) Repetitive rating 50mm x 50mm x 1.6mm FR4 PCB, D=0.02 pulse width=300μs - pulse width limited by maximum junction temperature.

(d) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

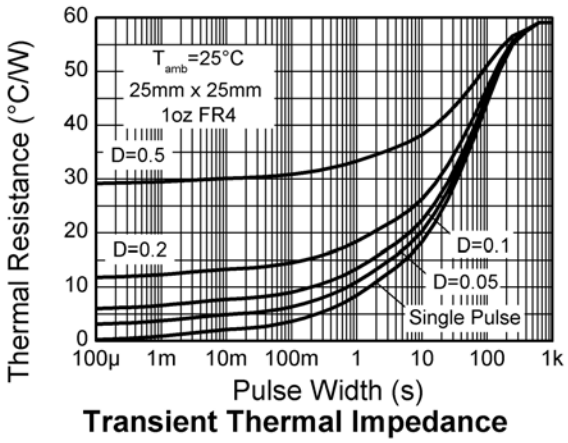
Thermal characteristics



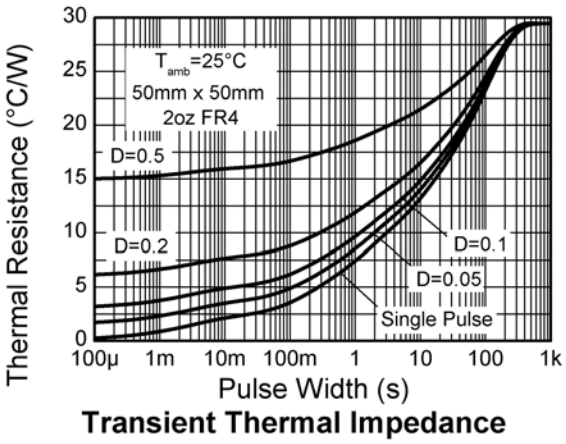
Safe Operating Area



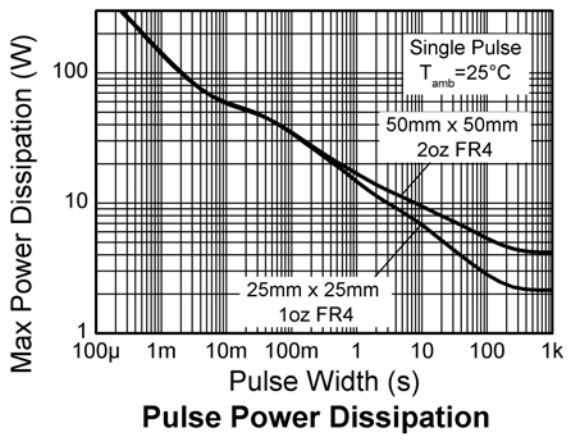
Safe Operating Area



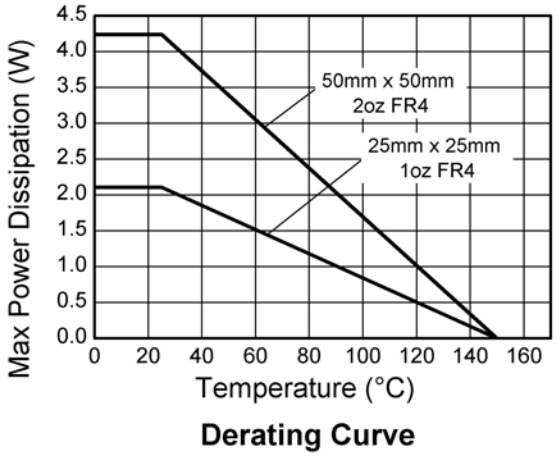
Transient Thermal Impedance



Transient Thermal Impedance



Pulse Power Dissipation



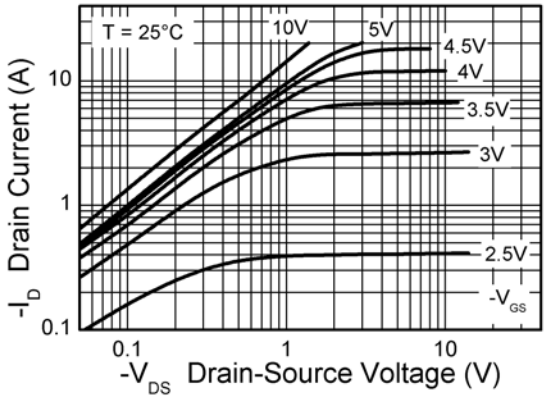
Derating Curve

Electrical characteristics (at T_{amb} = 25°C unless otherwise stated)

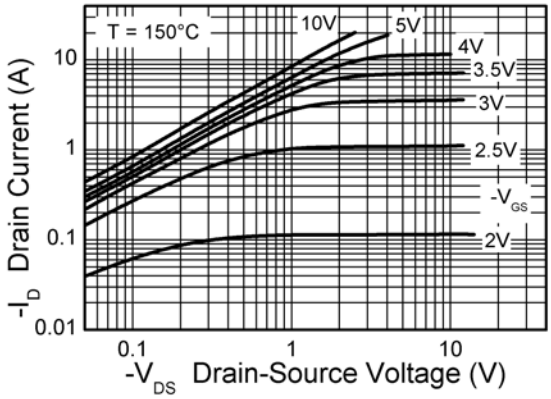
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	-60			V	I_D= -250μA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}			-1.0	μA	V_{DS}= -60V, V_{GS}=0V
Gate-body leakage	I_{GSS}			100	nA	V_{GS}=±20V, V_{DS}=0V
Gate-source threshold voltage	$V_{GS(th)}$	-1.0			V	I_D= -250μA, V_{DS}=VGS
Static drain-source on-state resistance (*)	$R_{DS(on)}$			0.085	Ω	V_{GS}= -10V, I_D= -2.9A
				0.125	Ω	V_{GS}= -4.5V, I_D = -2.4A
Forward transconductance(*) (‡)	g_{fs}		7.2		S	V_{DS}= -15V, I_D= -2.9A
Dynamic(‡)						
Input capacitance	C_{iss}		1021		pF	V_{DS}= -30V, V_{GS}=0V f=1MHz
Output capacitance	C_{oss}		83		pF	
Reverse transfer capacitance	C_{rss}		56		pF	
Switching (†) (‡)						
Turn-on-delay time	$t_{d(on)}$		3.5		ns	V_{DD}= -30V, I_D= -1A R_G≅6.0Ω, V_{GS}= -10V
Rise time	t_r		4.1		ns	
Turn-off delay time	$t_{d(off)}$		35		ns	
Fall time	t_f		10		ns	
Gate charge	Q_g		12.1		nC	V_{DS}= -30V, V_{GS}= -5V I_D= -2.9A
Total gate charge	Q_g		24.2		nC	V_{DS}= -30V, V_{GS}= -10V I_D= -2.9A
Gate-source charge	Q_{gs}		2.5		nC	
Gate drain charge	Q_{gd}		3.7		nC	
Source-drain diode						
Diode forward voltage(*)	V_{SD}		-0.85	-0.95	V	T_j=25°C, I_S= -3.4A, V_{GS}=0V
Reverse recovery time(‡)	t_{rr}		29.2		ns	T_j=25°C, I_S= -2A, di/dt=100A/μs
Reverse recovery charge(‡)	Q_{rr}		39.6		nC	

NOTES:
(*) Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.
(†) Switching characteristics are independent of operating junction temperature.
(‡) For design aid only, not subject to production testing.

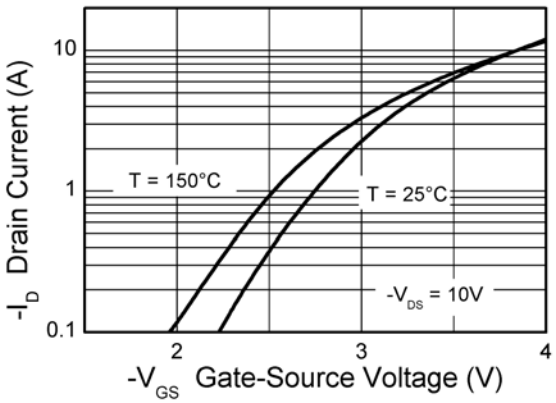
Typical characteristics



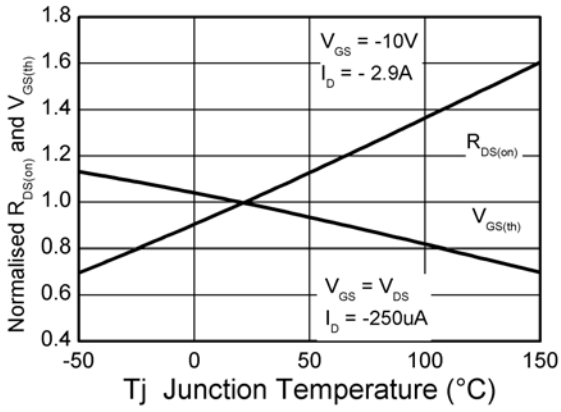
Output Characteristics



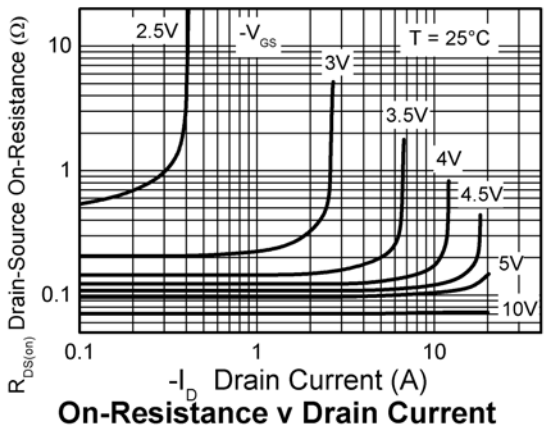
Output Characteristics



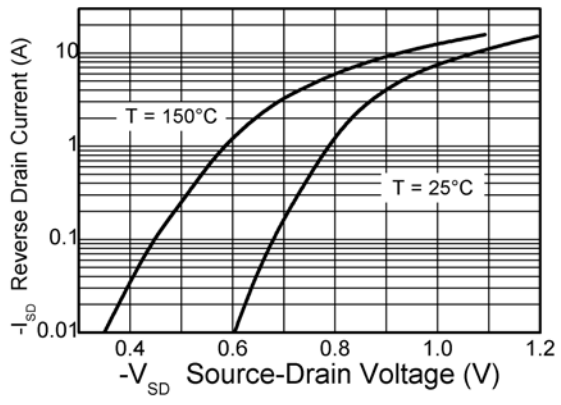
Typical Transfer Characteristics



Normalised Curves v Temperature

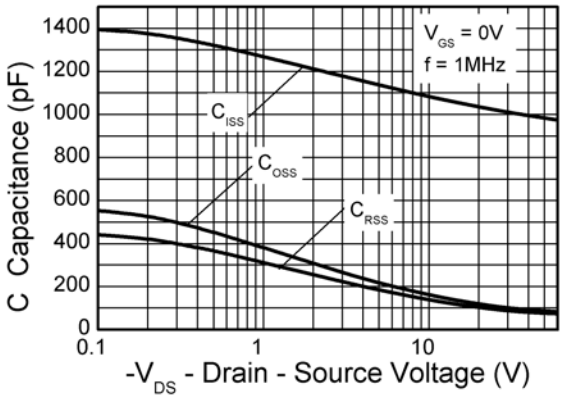


On-Resistance v Drain Current

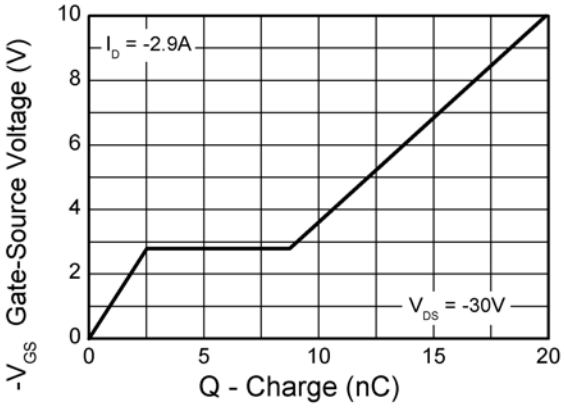


Source-Drain Diode Forward Voltage

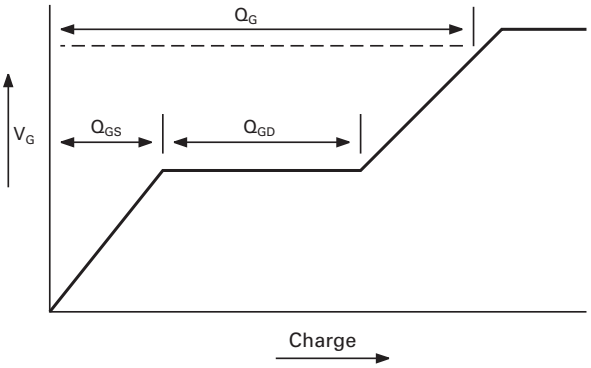
Typical characteristics



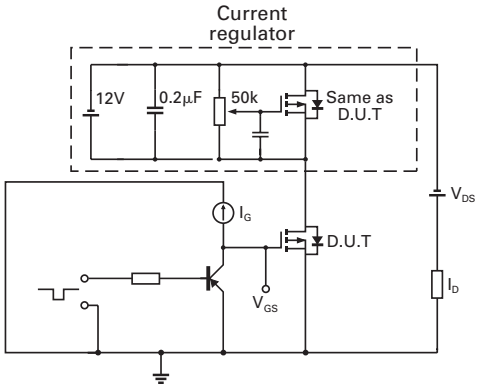
Capacitance v Drain-Source Voltage



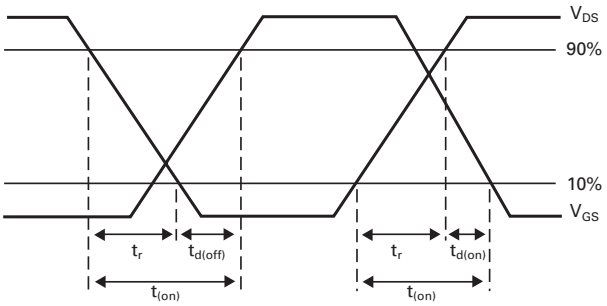
Gate-Source Voltage v Gate Charge

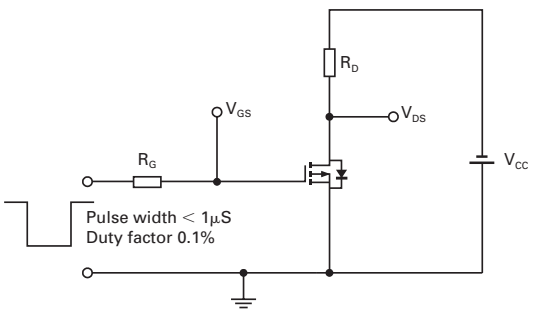


Basic gate charge waveform

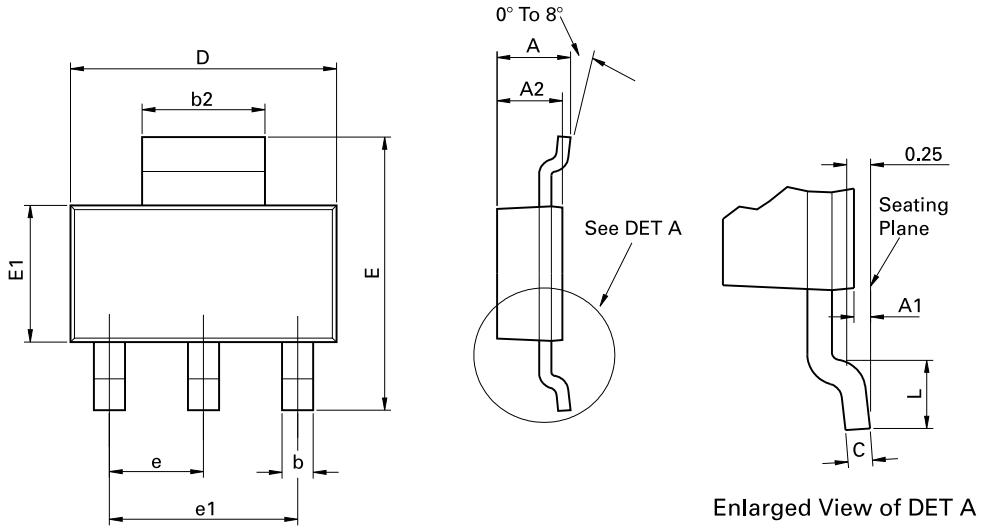


Gate charge test circuit





Package outline



Conforms to JEDEC TO-261 AA Issue B

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	-	1.80	-	0.071	e	2.30 BSC		0.0905 BSC	
A1	0.02	0.10	0.0008	0.004	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-
D	6.30	6.70	0.248	0.264	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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"Obsolete"	Production has been discontinued

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